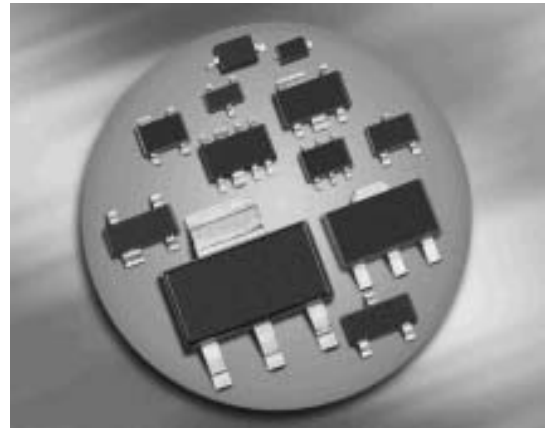
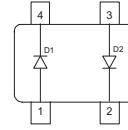
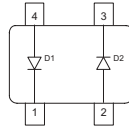
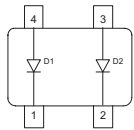
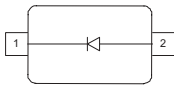


Silicon PIN Diode

- Optimized for low current antenna switches in hand held applications
- Very low forward resistance (typ. 1.5Ω @ $I_F = 1 \text{ mA}$)
- Low capacitance at zero volt reverse bias at frequencies above 1 GHz (typ. 0.28 pF)
- Very low signal distortion
- Pb-free (RoHS compliant) package ¹⁾
- Qualified according AEC Q101


BAR88-02LRH
BAR88-02V
BAR88-07LRH
BAR88-099LRH
BAR88-098LRH


Type	Package	Configuration	L_S (nH)	Marking
BAR88-02LRH	TSLP-2-7	single, leadless	0.4	U8
BAR88-02V	SC79	single	0.6	U
BAR88-07LRH	TSLP-4-7	parallel pair, leadless	0.4	T8
BAR88-098LRH	TSLP-4-7	anti-parallel, leadless	0.4	98
BAR88-099LRH	TSLP-4-7	anti parallel, leadless	0.4	S8

¹Pb-containing package may be available upon special request

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	80	V
Forward current	I_F	100	mA
Total power dissipation BAR88-02LRH, -07LRH $T_S \leq 133^\circ\text{C}$ BAR88-02V, $T_S \leq 123^\circ\text{C}$ BAR88-098LRH, -099LRH $T_S \leq 133^\circ\text{C}$	P_{tot}	250 250 250	mW
Junction temperature	T_j	150	°C
Operating temperature range	T_{op}	-55 ... 125	
Storage temperature	T_{stg}	-55 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾ BAR88-02LRH, -07LRH BAR88-02V BAR88-098LRH, -099LRH	R_{thJS}	≤ 65 ≤ 105 ≤ 65	K/W

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Breakdown voltage $I_{(\text{BR})} = 5 \mu\text{A}$	$V_{(\text{BR})}$	80	-	-	V
Reverse current $V_R = 60 \text{ V}$	I_R	-	-	50	nA
Forward voltage $I_F = 1 \text{ mA}$ $I_F = 100 \text{ mA}$	V_F	- -	0.75 0.95	0.9 1.2	V

¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

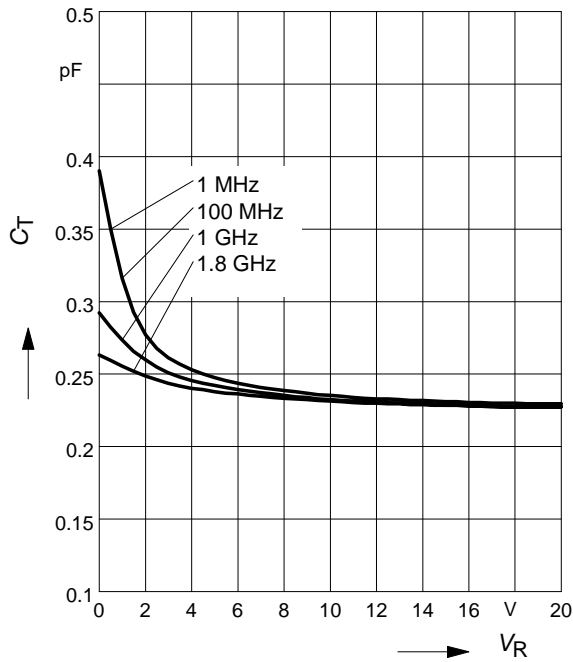
Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Diode capacitance $V_R = 1\text{ V}, f = 1\text{ MHz}$ $V_R = 0\text{ V}, f = 100\text{ MHz}$ $V_R = 0\text{ V}, f = 1\text{ GHz}$ $V_R = 0\text{ V}, f = 1.8\text{ GHz}$	C_T	-	0.3	0.4	pF
Reverse parallel resistance $V_R = 0\text{ V}, f = 100\text{ MHz}$ $V_R = 0\text{ V}, f = 1\text{ GHz}$ $V_R = 0\text{ V}, f = 1.8\text{ GHz}$	R_P	-	65	-	k Ω
Forward resistance $I_F = 1\text{ mA}, f = 100\text{ MHz}$ $I_F = 5\text{ mA}, f = 100\text{ MHz}$ $I_F = 10\text{ mA}, f = 100\text{ MHz}$	r_f	-	1.5	2.5	Ω
Charge carrier life time $I_F = 10\text{ mA}, I_R = 6\text{ mA}$, measured at $I_R = 3\text{ mA}$, $R_L = 100\ \Omega$	τ_{rr}	-	500	-	ns
I-region width	W_I	-	13	-	μm
Insertion loss ¹⁾ $I_F = 1\text{ mA}, f = 1.8\text{ GHz}$ $I_F = 5\text{ mA}, f = 1.8\text{ GHz}$ $I_F = 10\text{ mA}, f = 1.8\text{ GHz}$	I_L	-	0.11	-	dB
Isolation ¹⁾ $V_R = 0\text{ V}, f = 0.9\text{ GHz}$ $V_R = 0\text{ V}, f = 1.8\text{ GHz}$ $V_R = 0\text{ V}, f = 2.45\text{ GHz}$	I_{SO}	-	15	-	
		-	11	-	
		-	9	-	

¹BAR88-02LRH in series configuration, $Z = 50\ \Omega$

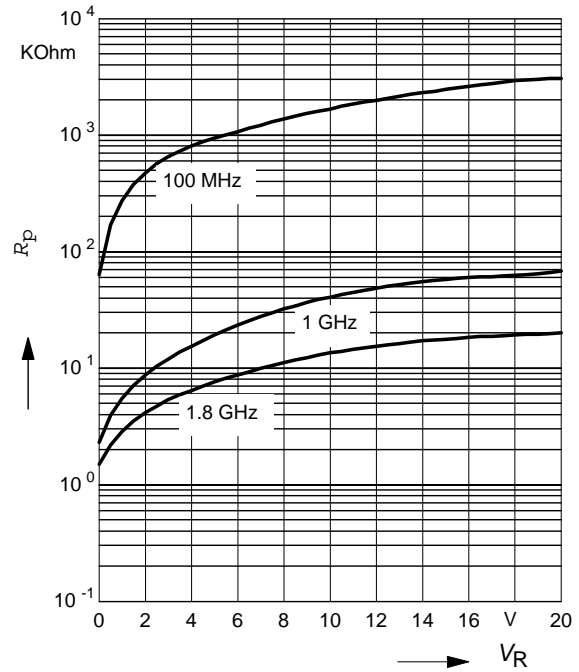
Diode capacitance $C_T = f(V_R)$

$f =$ Parameter



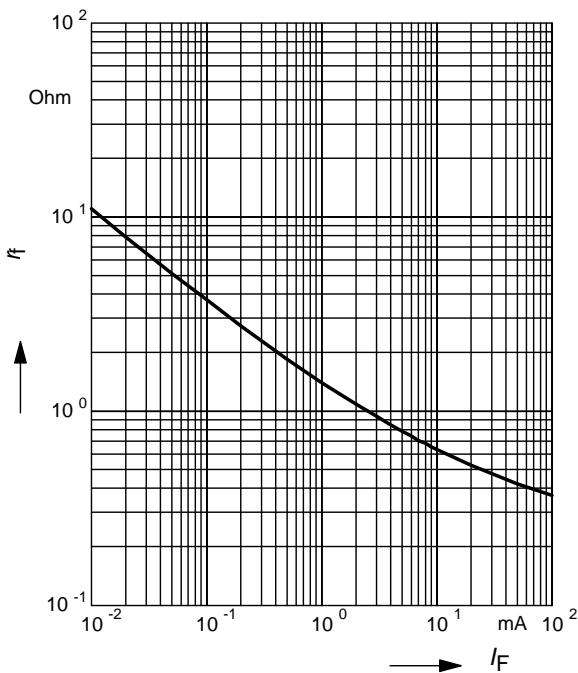
Reverse parallel resistance $R_p = f(V_R)$

$f =$ Parameter



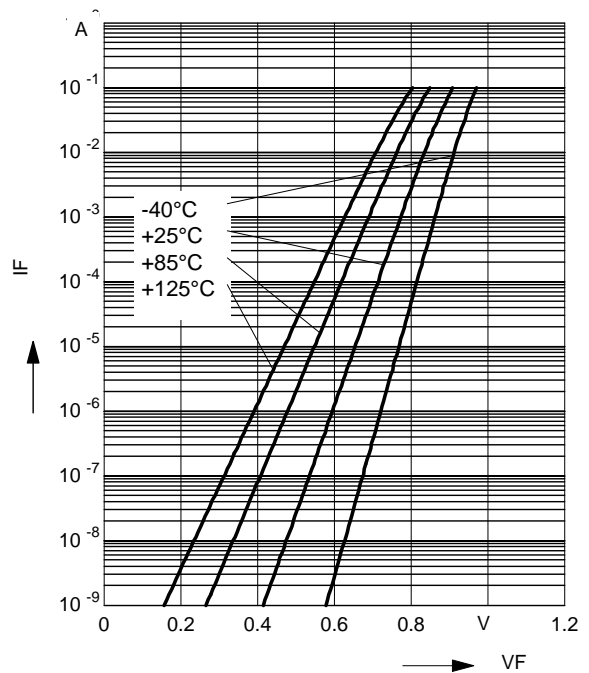
Forward resistance $r_f = f(I_F)$

$f = 100\text{MHz}$



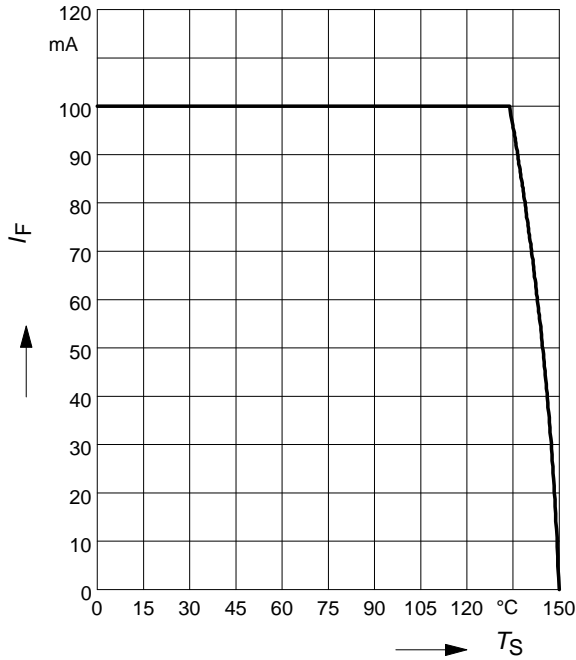
Forward current $I_F = f(V_F)$

$T_A =$ Parameter



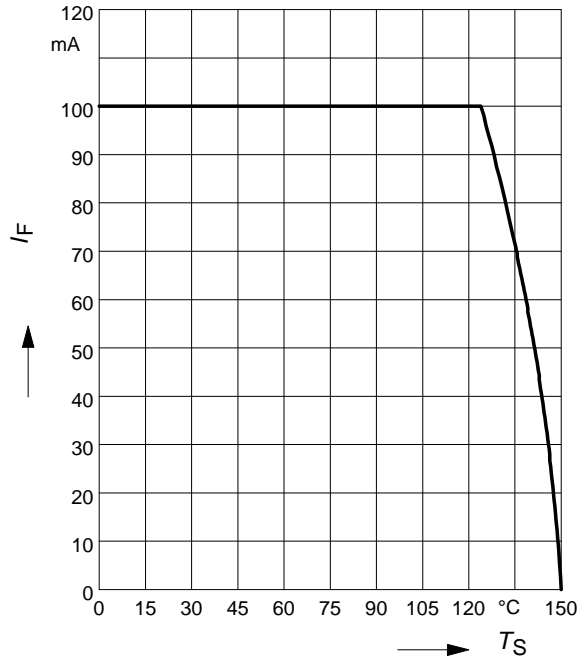
Forward current $I_F = f(T_S)$

BAR88-02LRH, -07LRH,
-098LRH, -099LRH



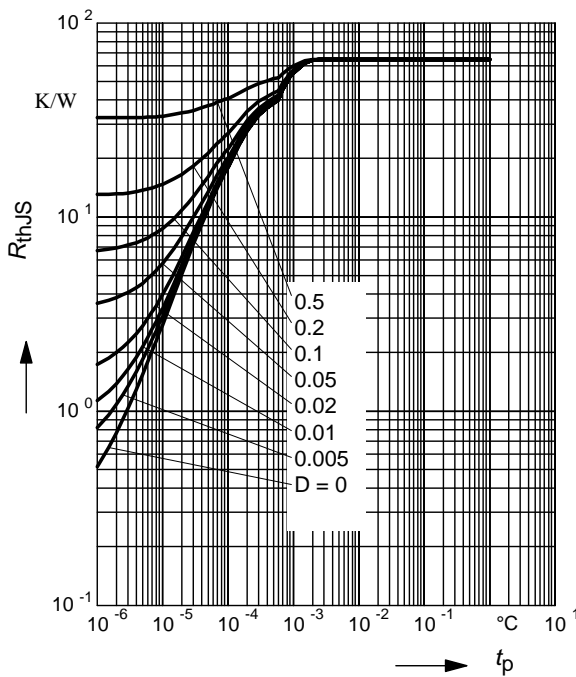
Forward current $I_F = f(T_S)$

BAR88-02V



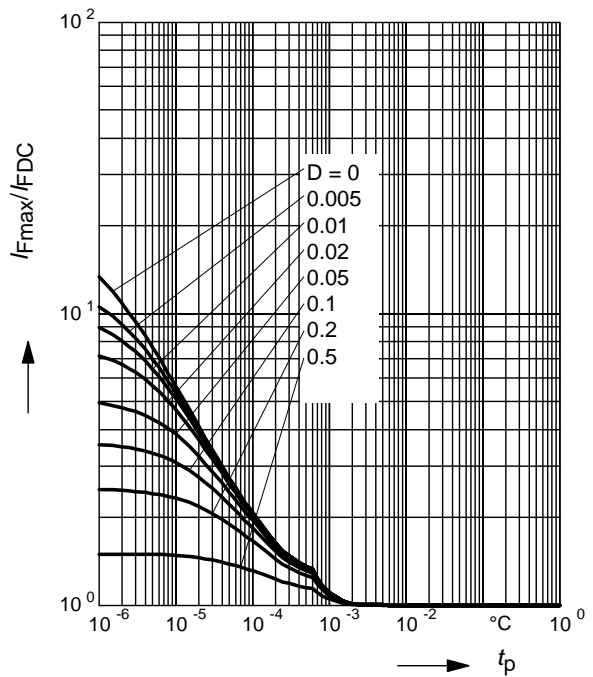
Permissible Puls Load $R_{thJS} = f(t_p)$

BAR88-02LRH, -07LRH
-098LRH, -099LRH



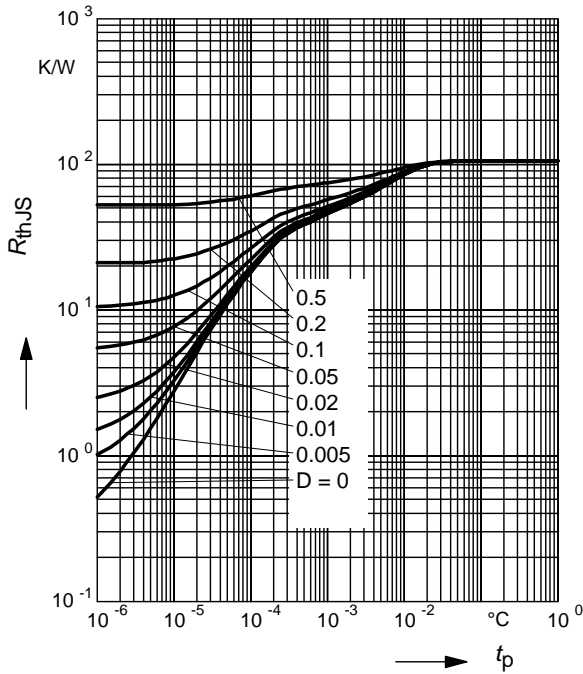
Permissible Pulse Load

$I_{Fmax}/I_{FDC} = f(t_p)$, BAR88-02LRH
-07LRH, -098LRH, -099LRH



Permissible Puls Load $R_{thJS} = f(t_p)$

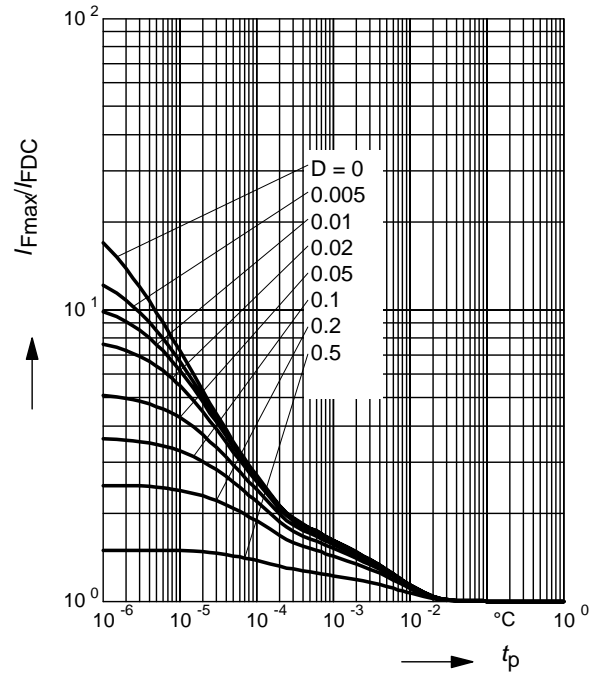
BAR88-02V



Permissible Pulse Load

$I_{Fmax} / I_{FDC} = f(t_p)$

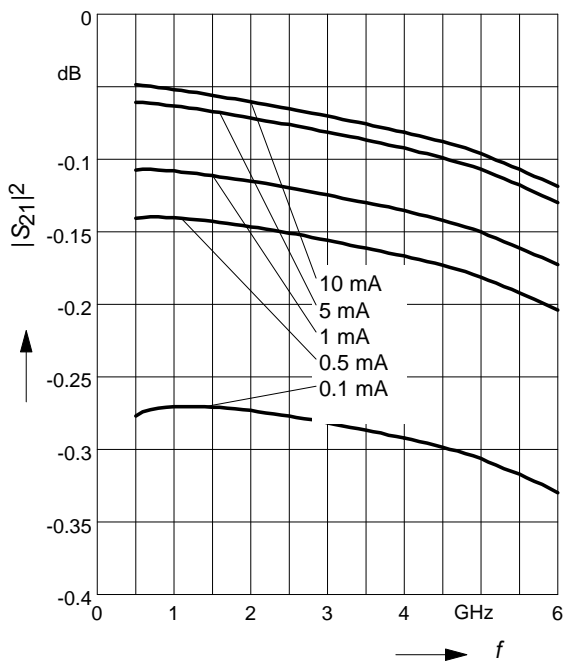
BAR88-02V



Insertion loss $I_L = -|S_{21}|^2 = f(f)$

I_F = Parameter

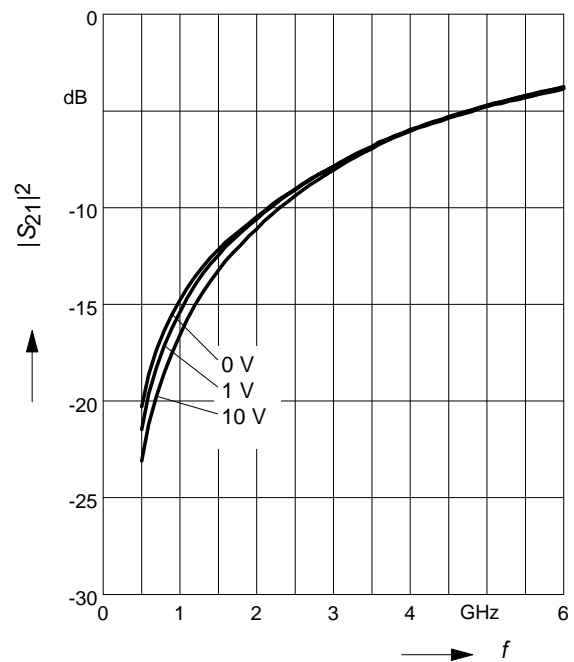
BAR88-02LRH in series configuration, $Z = 50\Omega$



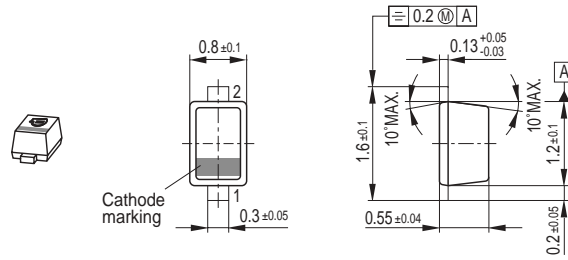
Isolation $I_{SO} = -|S_{21}|^2 = f(f)$

V_R = Parameter

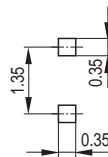
BAR88-02LRH in series configuration, $Z = 50\Omega$



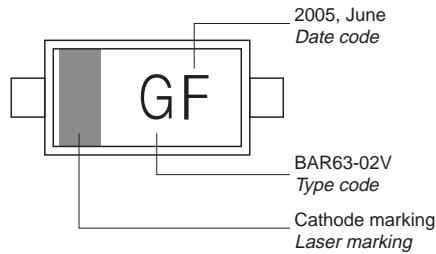
Package Outline



Foot Print

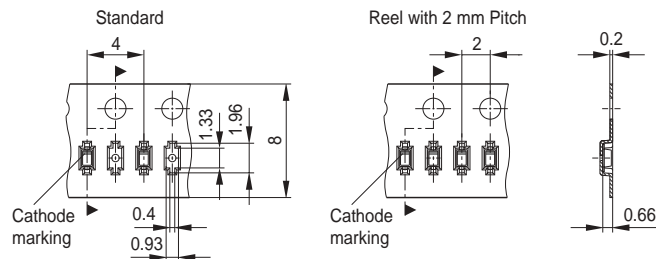


Marking Layout (Example)



Standard Packing

Reel \varnothing 180 mm = 3.000 Pieces/Reel
 Reel \varnothing 180 mm = 8.000 Pieces/Reel (2 mm Pitch)
 Reel \varnothing 330 mm = 10.000 Pieces/Reel

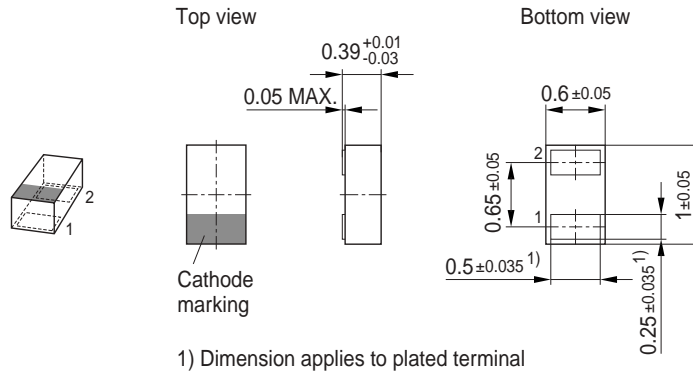


Date Code marking for discrete packages with one digit (SCD80, SC79, SC75¹⁾) CES-Code

Month	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014
01	a	p	A	P	a	p	A	P	a	p	A	P
02	b	q	B	Q	b	q	B	Q	b	q	B	Q
03	c	r	C	R	c	r	C	R	c	r	C	R
04	d	s	D	S	d	s	D	S	d	s	D	S
05	e	t	E	T	e	t	E	T	e	t	E	T
06	f	u	F	U	f	u	F	U	f	u	F	U
07	g	v	G	V	g	v	G	V	g	v	G	V
08	h	x	H	X	h	x	H	X	h	x	H	X
09	j	y	J	Y	j	y	J	Y	j	y	J	Y
10	k	z	K	Z	k	z	K	Z	k	z	K	Z
11	l	2	L	4	l	2	L	4	l	2	L	4
12	n	3	N	5	n	3	N	5	n	3	N	5

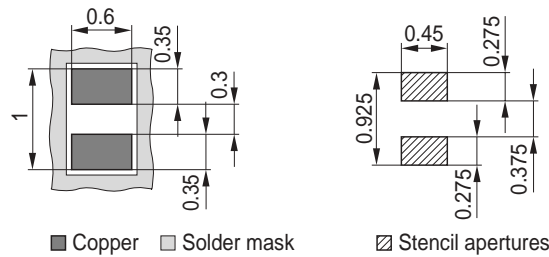
1) New Marking Layout for SC75, implemented at October 2005.

Package Outline

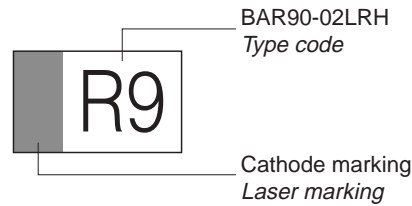


Foot Print

For board assembly information please refer to Infineon website "Packages"

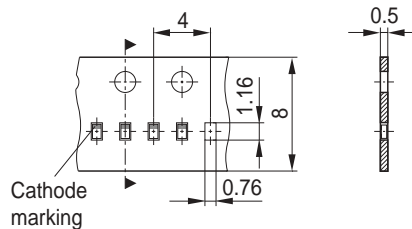


Marking Layout (Example)

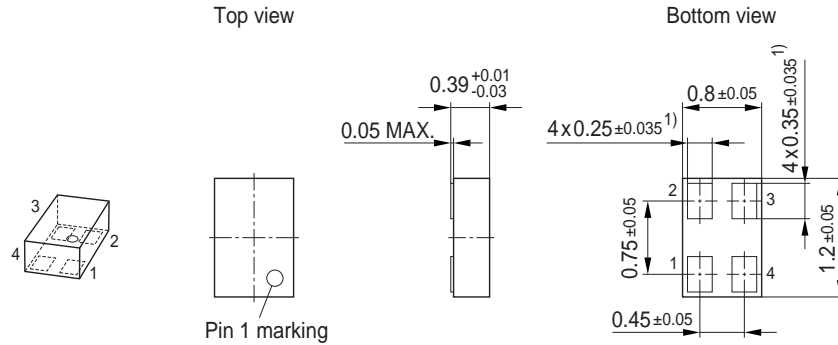


Standard Packing

Reel ø180 mm = 15.000 Pieces/Reel
 Reel ø330 mm = 50.000 Pieces/Reel (optional)



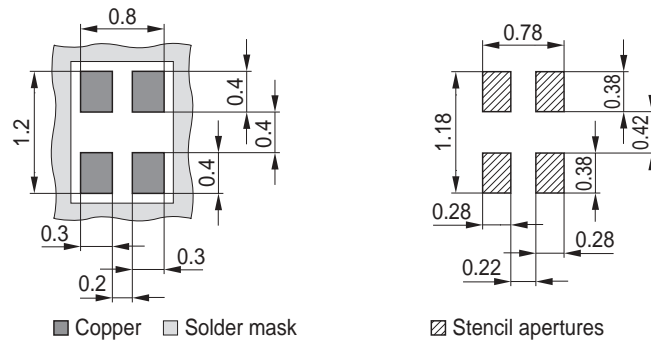
Package Outline



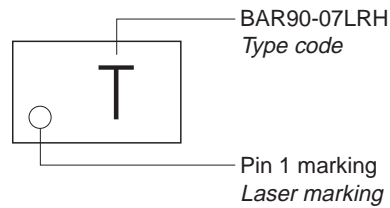
1) Dimension applies to plated terminal

Foot Print

For board assembly information please refer to Infineon website "Packages"

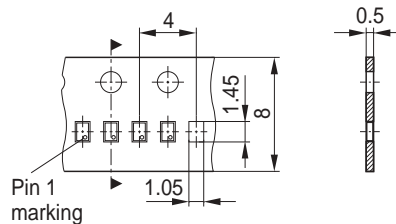


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 15.000 Pieces/Reel



Edition 2006-02-01
Published by
Infineon Technologies AG
81726 München, Germany
© Infineon Technologies AG 2007.
All Rights Reserved.

Attention please!

The information given in this dokument shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffheitsgarantie"). With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system.

Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.